# **MMBT2907A**



## MMBT2907A SOT-23 Plastic-Encapsulate Transistors (PNP)

#### **General description**

SOT-23 Plastic-Encapsulate Transistors (PNP)

#### **FEATURES**

- Complementary to MMBT2907A
- Power Dissipation of 250mW
- · High Stability and High Reliability
- SOT-23 Small Outline Plastic Package
- Epoxy UL: 94V-0

**DEVICE MARKING CODE: 2F** 



#### Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

Parameters	Symbol	Value	Unit	
Collector-Base Voltage	VCBO	-60	V	
Collector-Emitter Voltage	VCEO	-60	V	
Emitter -Base Voltage	VEBO	-5	V	
Collector Current-Continuous	IC	-600	mA	
Collector Power Dissipation	PC	250	mW	
Junction Temperature	Tj	150	℃	
Storage Temperature	Tstg	-55-+150	$^{\circ}$ C	
Thermal resistance from junction to ambient	RθJA	500	°C/W	

#### **Electrical Characteristics** (Ratings at 25°C ambient temperature unless otherwise specified).

Parameter S	Symbolo	Test Condition	Limits		Unit
	Symbols		Min	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC=-100uA, IE=0	-60		V
Collector-emitter breakdown voltage	V(BR)CEO *	IC=-1mA, IB=0	-60		V
Emitter-base breakdown voltage Collector cut-off current Emitter cut-off current Collector cut-off current	V(BR)EBO	IE=-10uA, IC=0	-5		V
	ІСВО	VCB=-50V, IE=0		-20	nA
	IEBO	VEB=-3V, IC=0		-10	nA
	ICEX	VCE=-30V, VBE(off)=-0.5V		-50	nA
DC current gain	hFE(1) *	VCE=-10V, IC=-150mA	100	300	
	hFE(2) *	VCE=-10V, IC=-0.1mA	75		
	hFE(3) *	VCE=-10V, IC=-1mA	100		
	hFE(4) *	VCE=-10V, IC=-10mA	100		
	hFE(5) *	VCE=-10V, IC=-500mA	50		
Collector-emitter saturation voltage	VCE(sat)1 *	IC=-150mA, IB=-15mA		-0.4	V
	VCE(sat)2 *	IC=-500mA, IB=-50mA		-1.6	V
Base -emitter saturation voltage	VBE(sat)1 *	IC=-150mA, IB=-15mA		-1.30	V
	VBE(sat)2 *	IC=-500mA, IB=-50mA		-2.60	V
Transition frequency	fT	VCE=-20V, IC=-50mA,f=100MHz	200		MHz
Delay time	td	1/05 201/ lo 450 A lo 45 A		10	nS
Rise time	tr	VCE=-30V, IC=-150mA, IB1=-15mA		25	nS
Storage time	ts	VCE=-6V, IC=-150mA, IB1=IB2=-		225	nS
Fall time	tf	15mA		60	nS

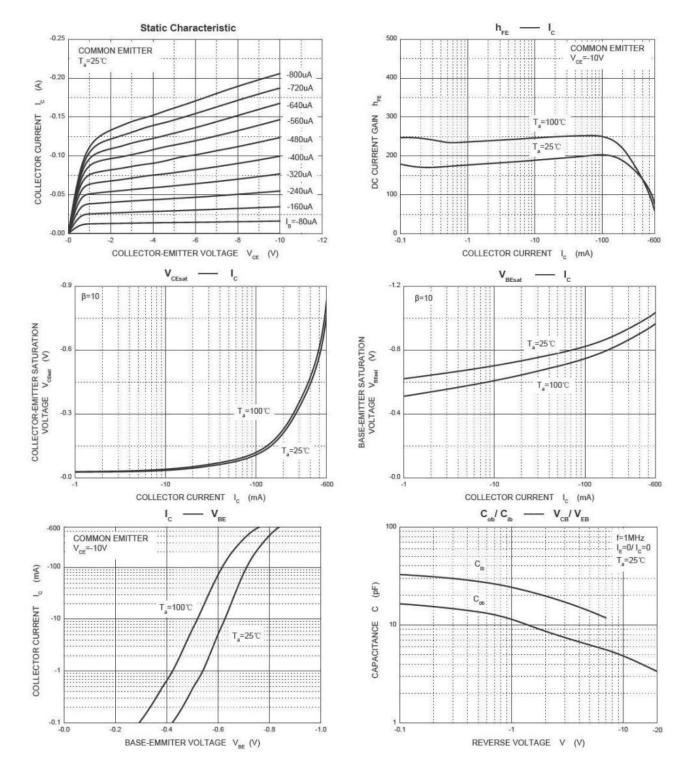
<sup>\*</sup>Pulse test: pulse width ≤300us, duty cycle ≤2.0%



#### **CLASSIFICATION OF hFE(1)**

HFE	100-300		
RANK	L	Н	
RANGE	100-200	200-300	

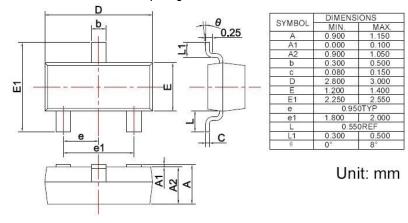
#### RATING AND CHARACTERISTIC CURVES



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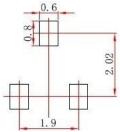


### SOT-23 PACKAGE OUTLINE Plastic surface mounted package



Precautions: PCB Design

Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



- Note: 1.Controlling dimension:in millimeters, 2.General tolerance:±0.05mm. 3.The pad layout is for reference purposes only.



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